

Jae-Keun Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Resistive Switching by Percolative Conducting Filaments in Organometal Perovskite Unipolar Memory Devices Analyzed Using Current Noise Spectra. <i>Advanced Functional Materials</i> , 2022, 32, 2107727.	14.9	8
2	Channel-Length-Modulated Avalanche Multiplication in Ambipolar WSe_2 Field-Effect Transistors. <i>ACS Nano</i> , 2022, 16, 5376-5383.	14.6	9
3	Crystallinity-dependent device characteristics of polycrystalline 2D $n = 4$ Ruddlesden-Popper perovskite photodetectors. <i>Nanotechnology</i> , 2021, 32, 185203.	2.6	10
4	Tailored Design-of-Experiments Approach for Device Performance Prediction and Optimization of Flash-Evaporated Organic-Inorganic Halide Perovskite-Based Photodetectors. <i>Advanced Materials Technologies</i> , 2021, 6, 2001131.	5.8	5
5	Perovskite Photodetector Devices: Tailored Design-of-Experiments Approach for Device Performance Prediction and Optimization of Flash-Evaporated Organic-Inorganic Halide Perovskite-Based Photodetectors (Adv. Mater. Technol. 5/2021). <i>Advanced Materials Technologies</i> , 2021, 6, 2170029.	5.8	0
6	Ultrasensitive Photodetection in MoS_2 Avalanche Phototransistors. <i>Advanced Science</i> , 2021, 8, e2102437.	11.2	34
7	Molecular Dopant-Dependent Charge Transport in Surface-Charge-Transfer-Doped Tungsten Diselenide Field Effect Transistors. <i>Advanced Materials</i> , 2021, 33, e2101598.	21.0	20
8	Role of Two-Dimensional Ising Superconductivity in the Nonequilibrium Quasiparticle Spin-to-Charge Conversion Efficiency. <i>ACS Nano</i> , 2021, 15, 16819-16827.	14.6	2
9	Introduction to Molecular Interface Engineering of Transition Metal Dichalcogenide-based Devices. , 2021, , 43-91.		0
10	Enhanced Output Performance of All-Solution-Processed Organic Thermoelectrics: Spray Printing and Interface Engineering. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 26250-26257.	8.0	10
11	Enhanced Photo-Response of MoS_2 Photodetectors by a Laterally Aligned SiO_2 Nanoribbon Array Substrate. <i>ChemNanoMat</i> , 2019, 5, 1272-1279.	2.8	2
12	Highly uniform monolayer graphene synthesis <i>via</i> a facile pretreatment of copper catalyst substrates using an ammonium persulfate solution. <i>RSC Advances</i> , 2019, 9, 20871-20878.	3.6	6
13	Intrinsic Optoelectronic Characteristics of MoS_2 Phototransistors <i>via</i> a Fully Transparent van der Waals Heterostructure. <i>ACS Nano</i> , 2019, 13, 9638-9646.	14.6	43
14	Dose-dependent effect of proton irradiation on electrical properties of WSe_2 ambipolar field effect transistors. <i>Nanoscale</i> , 2019, 11, 13961-13967.	5.6	5
15	Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping. <i>Advanced Materials</i> , 2019, 31, e1806697.	21.0	60
16	Organic Field-Effect Transistors: Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping (Adv. Mater. 10/2019). <i>Advanced Materials</i> , 2019, 31, 1970073.	21.0	2
17	Trapped charge modulation at the MoS_2/SiO_2 interface by a lateral electric field in MoS_2 field-effect transistors. <i>Nano Futures</i> , 2019, 3, 011002.	2.2	13
18	Effect of Facile p-Doping on Electrical and Optoelectronic Characteristics of Ambipolar WSe_2 Field-Effect Transistors. <i>Nanoscale Research Letters</i> , 2019, 14, 313.	5.7	9

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19	Contact-Engineered Electrical Properties of MoS ₂ Field-Effect Transistors via Selectively Deposited Thiol-Molecules. <i>Advanced Materials</i> , 2018, 30, e1705540.	21.0	56
20	Field-Effect Transistors: Contact-Engineered Electrical Properties of MoS ₂ Field-Effect Transistors via Selectively Deposited Thiol-Molecules (<i>Adv. Mater.</i> 18/2018). <i>Advanced Materials</i> , 2018, 30, 1870129.	21.0	1
21	Effects of Electron Beam Irradiation and Thiol Molecule Treatment on the Properties of MoS ₂ Field Effect Transistors. <i>Journal of the Korean Physical Society</i> , 2018, 72, 1203-1208.	0.7	7
22	Two-Dimensional Thickness-Dependent Avalanche Breakdown Phenomena in MoS ₂ Field-Effect Transistors under High Electric Fields. <i>ACS Nano</i> , 2018, 12, 7109-7116.	14.6	43
23	Analysis of the interface characteristics of CVD-grown monolayer MoS ₂ by noise measurements. <i>Nanotechnology</i> , 2017, 28, 145702.	2.6	14
24	Analysis of noise generation and electric conduction at grain boundaries in CVD-grown MoS ₂ field effect transistors. <i>Nanotechnology</i> , 2017, 28, 47LT01.	2.6	9
25	Transparent Large-Area MoS ₂ Phototransistors with Inkjet-Printed Components on Flexible Platforms. <i>ACS Nano</i> , 2017, 11, 10273-10280.	14.6	72
26	Trap-mediated electronic transport properties of gate-tunable pentacene/MoS ₂ p-n heterojunction diodes. <i>Scientific Reports</i> , 2016, 6, 36775.	3.3	54
27	Electrical and Optical Characterization of MoS ₂ with Sulfur Vacancy Passivation by Treatment with Alkanethiol Molecules. <i>ACS Nano</i> , 2015, 9, 8044-8053.	14.6	185
28	Enhancement of photodetection characteristics of MoS ₂ field effect transistors using surface treatment with copper phthalocyanine. <i>Nanoscale</i> , 2015, 7, 18780-18788.	5.6	101